## MICROWAVE POWER GAN HEMT

# TG17785-60LHA

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

- **BROAD BAND INTERNALLY MATCHED HEMT**
- ·HIGH POWER

Pout= 48.0dBm at Pin= 41dBm

·HIGH GAIN

GL= 11.5dB at Pin= 20dBm

·LOW INTERMODULATION DISTORTION WITH WIDE SPACING TONE IM3= -25dBc(Min.) at Pout= 29dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 40V IDSset= 0.4A f= 7.7 to 8.5GHz @Pin= 41dBm	dBm	47.0	48.0	_
Drain Current	IDS1		Α	_	4.0	4.5
Power Added Efficiency	ηadd		%	_	32	
Linear Gain	GL	@Pin= 20dBm	dB	10.5	11.5	_
Gain flatness	ΔG		dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 41dBm, (Single Carrier Level) Δf= 5MHz (IM3) Δf= 150MHz (IM3-2)	dBc	-25	-30	_
	IM3-2		dBc	-25	-27	_
Drain Current	IDS2		Α	_	2.0	2.5
Channel Temperature Rise *1	ΔTch		°C	_	120	140

#### Recommended Gate Resistance(Rg):10 $\Omega$

# **ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	_	4.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 15mA	V	-2.0	-3.0	-5.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	Α	_	10	_
Gate-Source Breakdown Voltage	VGSO	IGS= -12mA	V	-10	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.6	1.8

<sup>♦</sup> The information contained herein is presented as guidance for product use. No responsibility is assumed by Toshiba Infrastructure Systems & Solutions Corporation (hereinafter, referred to as "TISS") for any infringement of patents or any other intellectual property rights of third parties that may result from the use of product. No license to any intellectual property right is granted by this document. The information contained herein is subject to change without prior notice. It is advisable to contact TISS before proceeding with design of equipment incorporating this product.

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

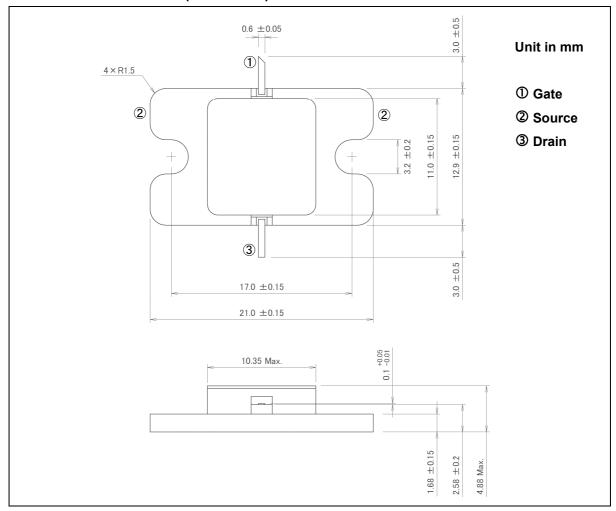
<sup>\*1:</sup>  $\triangle Tch = (VDS \times IDS2 + Pin(two-tone) - Po(two-tone)) \times Rth(c-c)$ , calculated using parameters of IM3 test



# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	6.0
Total Power Dissipation (Tc= 25 °C)	PT	W	111
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

# PACKAGE OUTLINE (7-AA04A)



## HANDLING PRECAUTIONS FOR PACKAGE MODEL

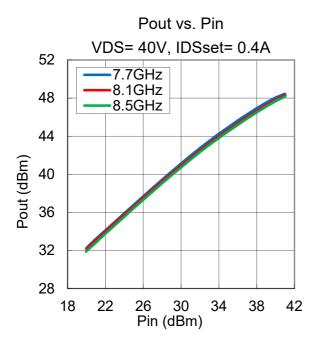
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

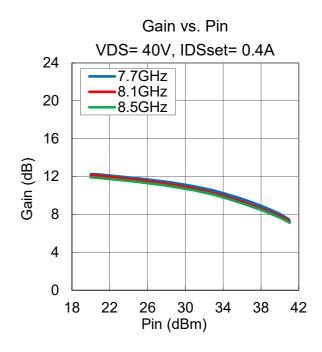


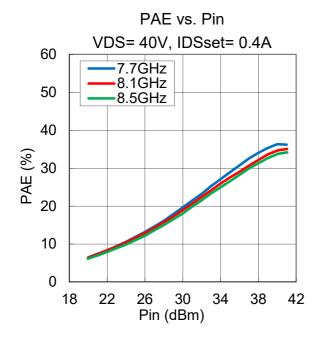
#### TYPICAL RF PERFORMANCE

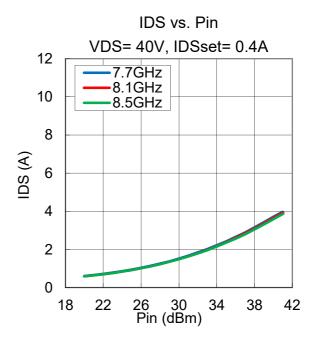
·Pout, Gain, PAE, IDS vs. Pin

VDS= 40V, IDSset= 0.4A, f= 7.7, 8.1, 8.5GHz, Ta= +25°C





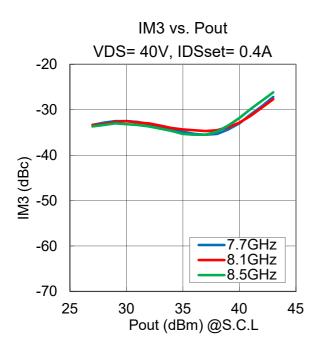


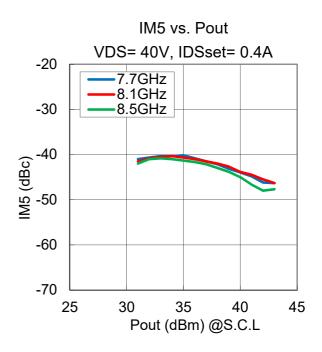




#### ·IM3, IM5 vs. Pout

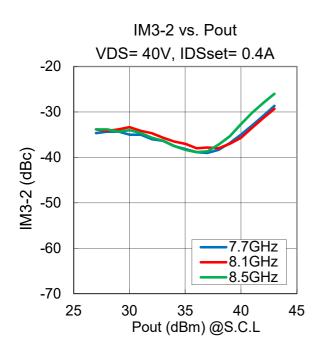
VDS= 40V, IDSset= 0.4A, f= 7.7, 8.1, 8.5GHz, Δf= 5MHz, Ta= +25°C

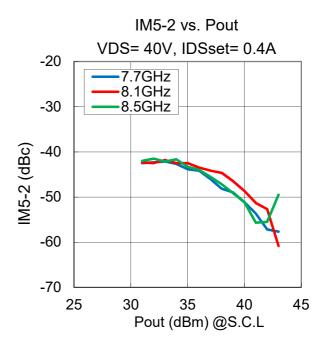




#### ·IM3, IM5 vs. Pout

VDS= 40V, IDSset= 0.4A, f= 7.7, 8.1, 8.5GHz, ∆f= 150MHz, Ta= +25°C

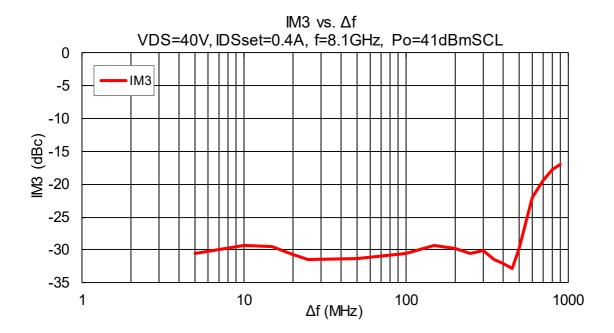






·IM3 vs.  $\Delta f$  (Two tone spacing)

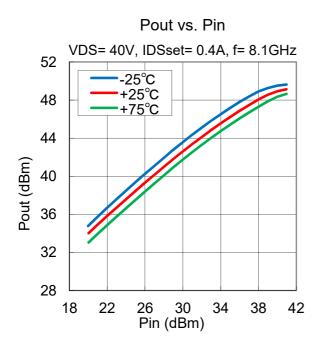
VDS= 40V, IDSset= 0.4A, f= 8.1GHz, Po= 41dBmSCL, Ta= +25°C

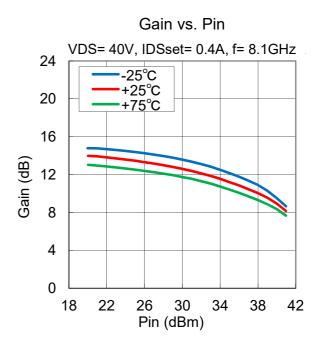


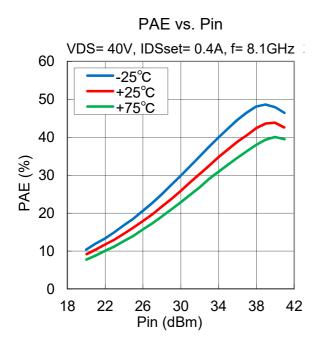


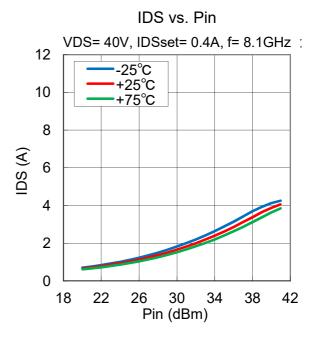
### ·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 40V, IDSset= 0.4A, f= 8.1GHz, Ta= -25, +25, +75°C





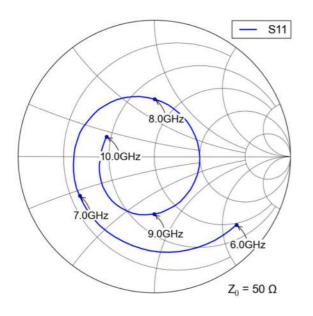


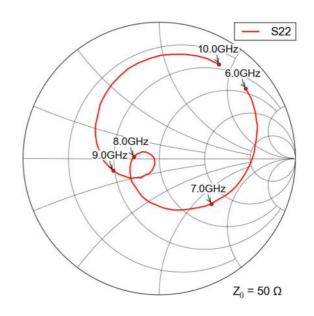


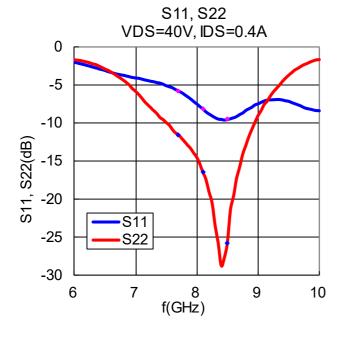


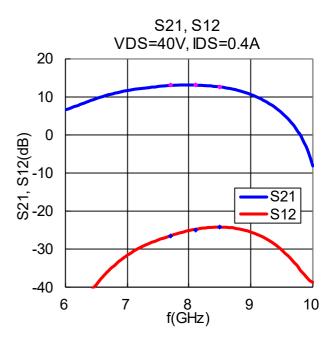
#### ·S-Parameter

VDS= 40V, IDSset= 0.4A, f= 6 to 10GHz, Ta= +25°C









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#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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